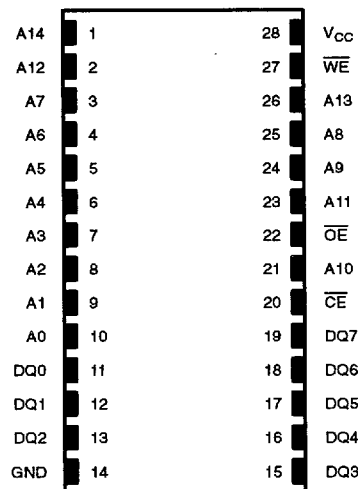
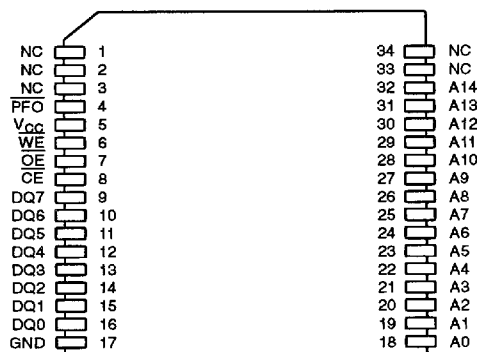


**DALLAS**  
**SEMICONDUCTOR**
**DS1730Y**  
**3-Volt Partitionable 256K NV SRAM**
**FEATURES**

- 10 years minimum data retention in the absence of external power
- Data is automatically protected during power loss
- Directly replaces 32K x 8 volatile static RAM or EEPROM
- Write protects selected blocks of memory when programmed
- Unlimited write cycles
- Low-power CMOS
- 2.7 volt to 3.6 volt operation
- Read and write access times as fast as 150 ns
- Lithium energy source is electrically disconnected to retain freshness until power is applied for the first time
- Optional industrial temperature range of -40°C to +85°C, designated IND
- JEDEC standard 28-pin DIP package
- Low Profile Module (LPM) package
  - Fits into standard 68-pin PLCC surface mountable socket
  - 255 mils package height
  - Power Fail Output ( $\overline{\text{PFO}}$ ) warns system of impending  $V_{CC}$  power failure

**PIN ASSIGNMENT**

 28-PIN ENCAPSULATED PACKAGE  
 740 MIL EXTENDED


34-PIN LOW PROFILE MODULE (LPM)

## PIN DESCRIPTION

A0 - A14	– Address Inputs
DQ0 - DQ7	– Data In/Data Out
$\overline{CE}$	– Chip Enable
$\overline{WE}$	– Write Enable
$\overline{OE}$	– Output Enable
PFO	– Power Fail Output (LPM only)
$V_{CC}$	– Power (2.7 to 3.6 volts)
GND	– Ground
NC	– No Connect

## DESCRIPTION

The DS1730 256K Nonvolatile SRAMs, are 262,144-bit, fully static, nonvolatile SRAMs organized as 32,768 words by 8 bits. Each NV SRAM has a self-contained lithium energy source and control circuitry which constantly monitors  $V_{CC}$  for an out-of-tolerance condition. When such a condition occurs, the lithium energy source is automatically switched on and write protection is unconditionally enabled to prevent data corruption. In addition, the device has the ability to unconditionally write protect blocks of memory so that inadvertent write cycles do not corrupt programs and important data. There is no limit on the number of write cycles that can be executed and no additional support circuitry is required for microprocessor interfacing. DIP-package DS1730 devices can be used in place of existing 32Kx8 SRAMs directly conforming to the popular byte-wide 28-pin DIP standard. The DIP devices also match the pinout of 28256 EEPROMs, allowing direct substitution while enhancing performance. DS1730 devices in the Low Profile Module package are specifically designed for surface mount applications. DS1730 LPM devices also have an additional pin, a Power Fail Output that can be used to warn a system of impending  $V_{CC}$  power failure.

## READ MODE

The DS1730 devices execute a read cycle whenever  $\overline{WE}$  (Write Enable) is inactive (high) and  $\overline{CE}$  (Chip Enable) and  $\overline{OE}$  (Output Enable) are active (low). The

unique address specified by the 15 address inputs ( $A_0$  -  $A_{14}$ ) defines which of the 32,768 bytes of data is to be accessed. Valid data will be available to the eight data output drivers within  $t_{ACC}$  (Access Time) after the last address input signal is stable, providing that  $\overline{CE}$  and  $\overline{OE}$  (Output Enable) access times are also satisfied. If  $\overline{OE}$  and  $\overline{CE}$  access times are not satisfied, then data access must be measured from the later occurring signal ( $\overline{CE}$  or  $\overline{OE}$ ) and the limiting parameter is either  $t_{CO}$  for  $\overline{CE}$  or  $t_{OE}$  for  $\overline{OE}$  rather than address access.

## WRITE MODE

The DS1730 devices execute a write cycle whenever the  $\overline{WE}$  and  $\overline{CE}$  signals are in the active (low) state after address inputs are stable. The latter occurring falling edge of  $\overline{CE}$  or  $\overline{WE}$  will determine the start of the write cycle. The write cycle is terminated by the earlier rising edge of  $\overline{CE}$  or  $\overline{WE}$ . All address inputs must be kept valid throughout the write cycle.  $\overline{WE}$  must return to the high state for a minimum recovery time ( $t_{WR}$ ) before another cycle can be initiated. The  $\overline{OE}$  control signal should be kept inactive (high) during write cycles to avoid bus contention. However, if the output drivers are enabled ( $\overline{CE}$  and  $\overline{OE}$  active) then  $\overline{WE}$  will disable the outputs in  $t_{ODW}$  from its falling edge.

## DATA RETENTION MODE

The DS1730Y device provides full functional capability for  $V_{CC}$  greater than 2.70 volts and write protects by 2.50 volts. Data is maintained in the absence of  $V_{CC}$  without any additional support circuitry. The nonvolatile static RAMs constantly monitor  $V_{CC}$ . Should the supply voltage decay, the NV SRAMs automatically write protect themselves, all inputs become "don't care," and all outputs become high impedance. As  $V_{CC}$  falls below approximately 2.6 volts, the power switching circuit connects the lithium energy source to RAM to retain data. During power-up, when  $V_{CC}$  rises above approximately 2.6 volts, the power switching circuit connects external  $V_{CC}$  to RAM and disconnects the lithium energy source. Normal RAM operation can resume after  $V_{CC}$  exceeds 2.70 volts.

### FRESHNESS SEAL

Each DS1730 is shipped from Dallas Semiconductor with its lithium energy source disconnected, guaranteeing full energy capacity. When  $V_{CC}$  is first applied and remains at a level greater than  $V_{TP}$ , the lithium energy source is enabled for battery backup operation.

### PARTITION PROGRAMMING MODE

The register controlling the partitioning logic is selected by recognition of a specific binary pattern which is sent on address lines A11 - A14. These address lines are the four upper order address lines being sent to RAM. The pattern is sent by 20 consecutive read cycles with the exact pattern as shown in Table 1. Pattern matching must be accomplished using read cycles; any write cycles will reset the pattern matching circuitry. If this pattern is matched perfectly, then the 21st through 24th

read cycles will load the partition register. Since there are 16 protectable partitions, the size of each partition is 32K/16 or 2Kx8. Each partition is represented by one of the 16 bits contained in the 21st through 24th read cycles as defined by A11 through A14 and shown in Table 2. A logical 1 in a bit location write protects the corresponding partition. A logical 0 in a bit location disables write protection. For example, if during the pattern match sequence bit 22 on address pin A12 was a 1, this would cause the partition register location for partition 5 to be set to a 1. This in turn would cause the DS1730 devices to internally inhibit  $\overline{WE}$  when A14 A13 A12 A11=0101. Note that while programming the partition register, data which is being accessed from the RAM should be ignored, since the purpose of the 24 read cycles is to program the partition register, not to access data from RAM.

**PATTERN MATCH TO WRITE PARTITION REGISTER Table 1**

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24
A11	1	0	1	1	1	1	0	0	1	1	1	0	0	0	0	0	1	1	0	1	X	X	X	X
A12	1	1	1	1	1	0	0	1	1	1	0	0	1	0	1	1	0	0	0	0	X	X	X	X
A13	1	1	1	1	0	0	1	1	1	0	0	1	0	1	0	1	0	0	0	1	X	X	X	X
A14	1	1	0	0	0	1	1	1	0	0	1	0	0	0	1	0	1	0	0	0	X	X	X	X

FIRST BITS ENTERED

LAST BITS ENTERED

**PARTITION REGISTER MAPPING Table 2**

Address Pin	Bit number in pattern match sequence	Partition Number	Address State Affected (A <sub>14</sub> A <sub>13</sub> A <sub>12</sub> A <sub>11</sub> )
A11	BIT 21	PARTITION 0	0000
A12	BIT 21	PARTITION 1	0001
A13	BIT 21	PARTITION 2	0010
A14	BIT 21	PARTITION 3	0011
A11	BIT 22	PARTITION 4	0100
A12	BIT 22	PARTITION 5	0101
A13	BIT 22	PARTITION 6	0110
A14	BIT 22	PARTITION 7	0111
A11	BIT 23	PARTITION 8	1000
A12	BIT 23	PARTITION 9	1001
A13	BIT 23	PARTITION 10	1010
A14	BIT 23	PARTITION 11	1011
A11	BIT 24	PARTITION 12	1100
A12	BIT 24	PARTITION 13	1101
A13	BIT 24	PARTITION 14	1110
A14	BIT 24	PARTITION 15	1111

**ABSOLUTE MAXIMUM RATINGS\***

Voltage on Any Pin Relative to Ground

-0.5V to +7.0V

Operating Temperature

0°C to 70°C, -40°C to +85°C for IND parts

Storage Temperature

-40°C to +70°C, -40°C to +85°C for IND parts

Soldering Temperature

260°C for 10 seconds

\* This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operation sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods of time may affect reliability.

**RECOMMENDED DC OPERATING CONDITIONS**(t<sub>A</sub>: See Note 10)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
DS1730Y Power Supply Voltage	V <sub>CC</sub>	2.7		3.6	V	
Logic 1	V <sub>IH</sub>	2.2		V <sub>CC</sub>	V	
Logic 0	V <sub>IL</sub>	0.0		+0.4	V	

**DC ELECTRICAL CHARACTERISTICS**(t<sub>A</sub>: See Note 10) (V<sub>CC</sub>=2.7V to 3.6V)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
Input Leakage Current	I <sub>IL</sub>	-1.0		+1.0	μA	
I/O Leakage Current CE ≥ V <sub>IH</sub> ≤ V <sub>CC</sub>	I <sub>IO</sub>	-1.0		+1.0	μA	
Output Current @ 2.2V	I <sub>OH</sub>	-0.5			mA	
Output Current @ 0.4V	I <sub>OL</sub>	2.0			mA	14
Standby Current CE = 2.2V	I <sub>CCS1</sub>		5.0	7.0	mA	
Standby Current CE = V <sub>CC</sub> - 0.5V	I <sub>CCS2</sub>		3.0	4.0	mA	
Operating Current	I <sub>CCO1</sub>			40	mA	
Write Protection Voltage	V <sub>TP</sub>	2.50	2.60	2.70	V	

**CAPACITANCE**(t<sub>A</sub> = 25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
Input Capacitance	C <sub>IN</sub>		5	10	pF	
Input/Output Capacitance	C <sub>I/O</sub>		5	10	pF	

■ 2614130 0013885 269 ■

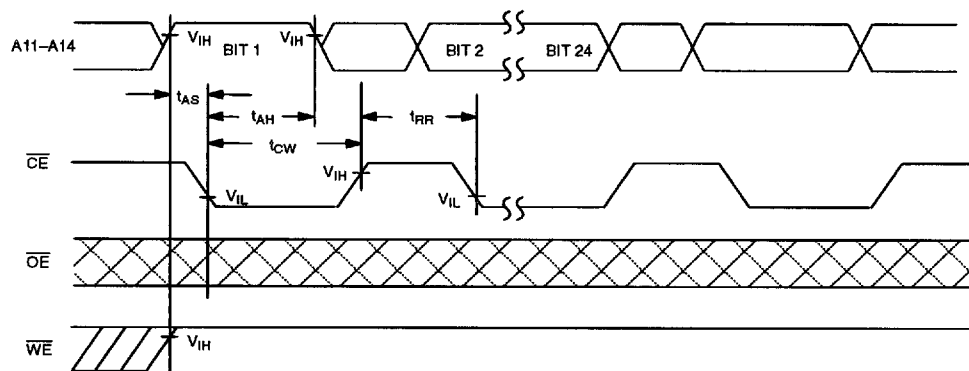
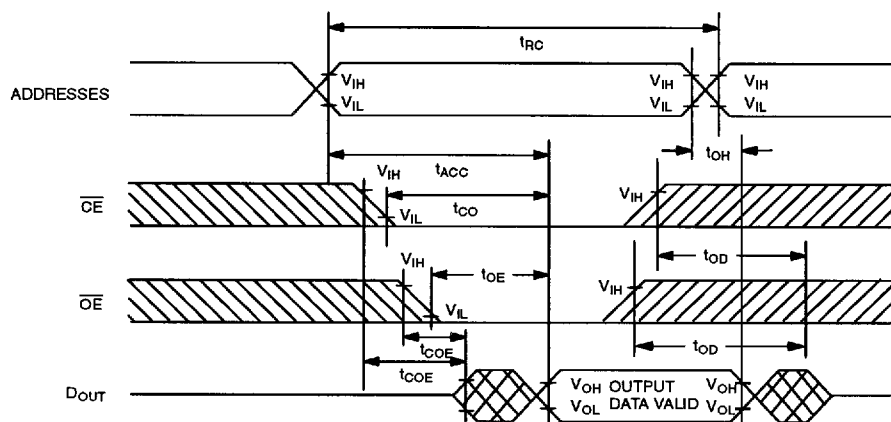
**AC ELECTRICAL CHARACTERISTICS**(t<sub>A</sub>: See Note 10) (V<sub>CC</sub>=2.7V to 3.6V)

PARAMETER	SYMBOL	DS1730Y-150		DS1730Y-200		UNITS	NOTES
		MIN	MAX	MIN	MAX		
Read Cycle Time	t <sub>RC</sub>	150		200		ns	
Access Time	t <sub>ACC</sub>		150		200	ns	
OE to Output Valid	t <sub>OE</sub>		70		100	ns	
CE to Output Valid	t <sub>CO</sub>		150		200	ns	
OE or CE to Output Valid	t <sub>COE</sub>	5		5		ns	5
Output High Z from Deselection	t <sub>OD</sub>		50		50	ns	5
Output Hold from Address Change	t <sub>OH</sub>	5		5		ns	
Write Cycle Time	t <sub>WC</sub>	150		200		ns	
Write Pulse Width	t <sub>WP</sub>	120		150		ns	3
Address Setup Time	t <sub>AW</sub>	0		0		ns	
Write Recovery Time	t <sub>WR1</sub>	10		10		ns	12
	t <sub>WR2</sub>	10		10		ns	13
Output High Z from WE	t <sub>ODW</sub>		50		50	ns	5
Output Active from WE	t <sub>OEWE</sub>	5		5		ns	5
Data Setup Time	t <sub>DS</sub>	60		80		ns	4
Data Hold Time	t <sub>DH1</sub>	10		10		ns	12
	t <sub>DH2</sub>	10		10		ns	13

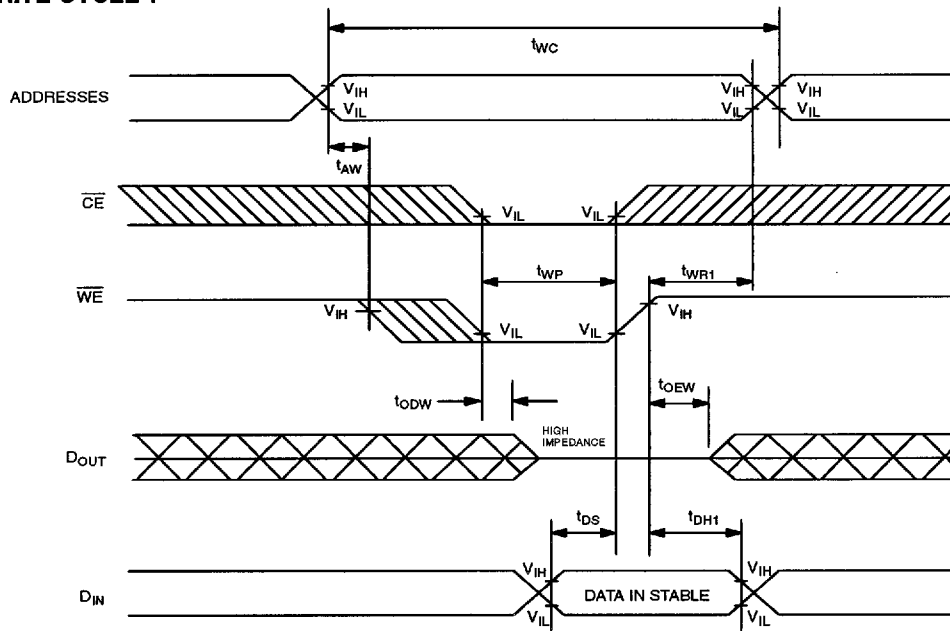
**AC ELECTRICAL CHARACTERISTICS**(t<sub>A</sub>: See Note 10) (V<sub>CC</sub>=2.7V to 3.6V)\*

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
Address Setup	t <sub>AS</sub>	0			ns	
Address Hold	t <sub>AH</sub>	50			ns	
Read Recovery	t <sub>RR</sub>	20			ns	
CE Pulse Width	t <sub>CW</sub>	75			ns	

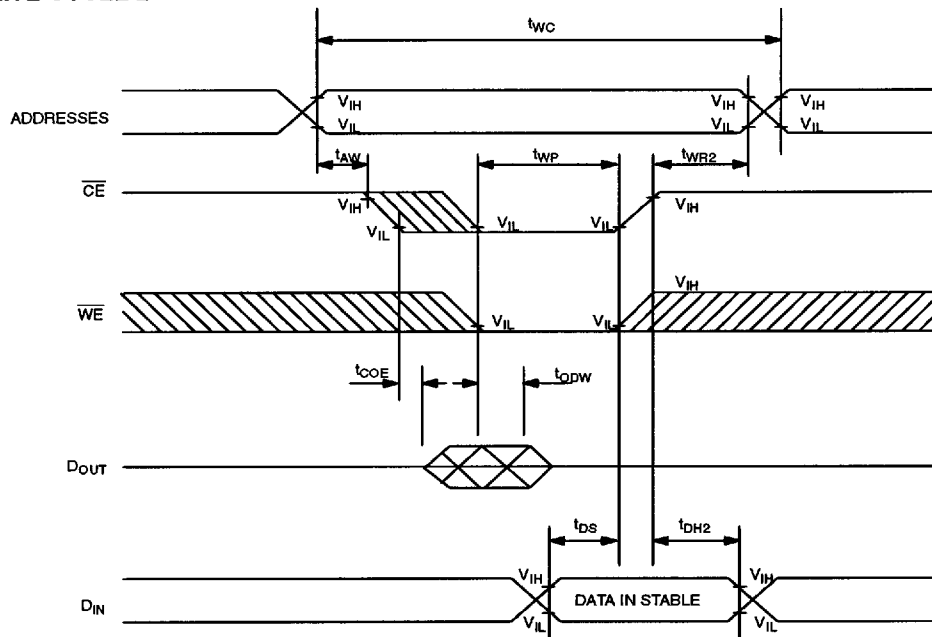
\*For loading partition register

**TIMING DIAGRAM: LOADING PARTITION REGISTER****READ CYCLE**

SEE NOTE 1

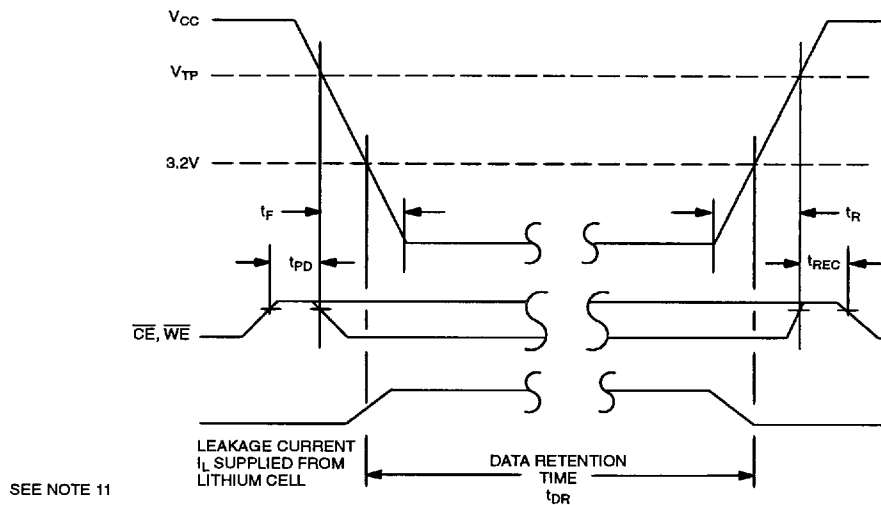
**WRITE CYCLE 1**

SEE NOTES 2, 3, 4, 6, 7, 8 AND 12

**WRITE CYCLE 2**

SEE NOTES 2, 3, 4, 6, 7, 8 AND 13



**POWER-DOWN/POWER-UP CONDITION****POWER-DOWN/POWER-UP TIMING**(t<sub>A</sub>: See Note 10)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
$\overline{CE}$ , $\overline{WE}$ at V <sub>IH</sub> before Power-Down	t <sub>PD</sub>	0			μs	11
V <sub>CC</sub> Slew from V <sub>TP</sub> to 0V ( $\overline{CE}$ at V <sub>IH</sub> )	t <sub>F</sub>	300			μs	
V <sub>CC</sub> Slew from 0V to V <sub>TP</sub> ( $\overline{CE}$ at V <sub>IH</sub> )	t <sub>R</sub>	0			μs	
$\overline{CE}$ , $\overline{WE}$ at V <sub>IH</sub> after Power-Up	t <sub>REC</sub>	100		200	ms	

(t<sub>A</sub> = 25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
Expected Data Retention Time	t <sub>DR</sub>	10			years	9

**WARNING:**

Under no circumstance are negative undershoots, of any amplitude, allowed when device is in battery backup mode.

**NOTES:**

1.  $\overline{WE}$  is high for a read cycle.
2.  $\overline{OE} = V_{IH}$  or  $V_{IL}$ . If  $\overline{OE} = V_{IH}$  during write cycle, the output buffers remain in a high impedance state.
3.  $t_{WP}$  is specified as the logical AND of  $\overline{CE}$  and  $\overline{WE}$ .  $t_{WP}$  is measured from the latter of  $\overline{CE}$  or  $\overline{WE}$  going low to the earlier of  $\overline{CE}$  or  $\overline{WE}$  going high.
4.  $t_{DS}$  is measured from the earlier of  $\overline{CE}$  or  $\overline{WE}$  going high.
5. These parameters are sampled with a 5 pF load and are not 100% tested.
6. If the  $\overline{CE}$  low transition occurs simultaneously with or later than the  $\overline{WE}$  low transition in Write Cycle 1, the output buffers remain in a high impedance state during this period.
7. If the  $\overline{CE}$  high transition occurs prior to or simultaneously with the  $\overline{WE}$  high transition, the output buffers remain in high impedance state during this period.
8. If  $\overline{WE}$  is low or the  $\overline{WE}$  low transition occurs prior to or simultaneously with the  $\overline{CE}$  low transition, the output buffers remain in a high impedance state during this period.
9. Each DS1730 has a built-in switch that disconnects the lithium source until  $V_{CC}$  is first applied by the user. The expected  $t_{DP}$  is defined as accumulative time in the absence of  $V_{CC}$  starting from the time power is first applied by the user.
10. All AC and DC electrical characteristics are valid over the full operating temperature range. For commercial products, this range is 0°C to 70°C. For industrial products (IND), this range is -40°C to +85°C.
11. In a power down condition the voltage on any pin may not exceed the voltage on  $V_{CC}$ .
12.  $t_{WR1}$ ,  $t_{DH1}$  are measured from  $\overline{WE}$  going high.
13.  $t_{WR2}$ ,  $t_{DH2}$  are measured from  $\overline{CE}$  going high.
14. The power fail output signal ( $\overline{PFO}$ ) is driven active ( $V_{OL}=0.4V$ ) when the  $V_{CC}$  trip point occurs. While active, the  $\overline{PFO}$  pin can sink 4 mA and will maintain a maximum output voltage of 0.4 volts. When inactive, the voltage output of  $\overline{PFO}$  is 2.4 volts minimum and will source a current of 1 mA. This signal is only present on the LPM package variations.

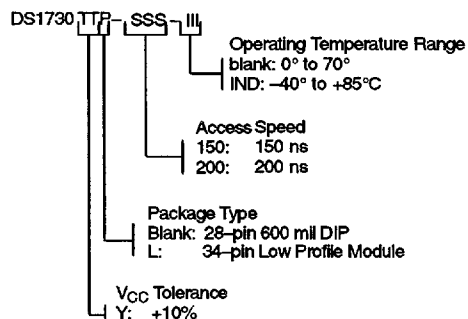
**DC TEST CONDITIONS**

Outputs Open  
Cycle = 200 ns  
All voltages are referenced to ground

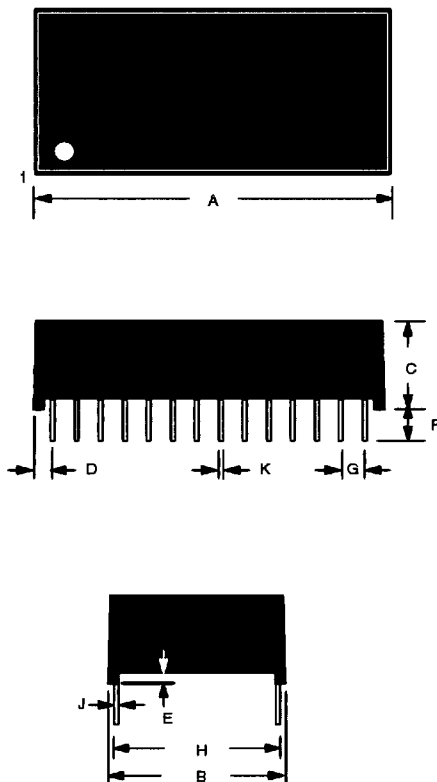
**AC TEST CONDITIONS**

Output Load: 100 pF + 1TTL Gate  
Input Pulse Levels:  
0.0 to 2.7 volts  
Timing Measurement Reference Levels  
Input: 1.5V  
Output: 1.5V  
Input Pulse Rise and Fall Times: 5 ns

## ORDERING INFORMATION

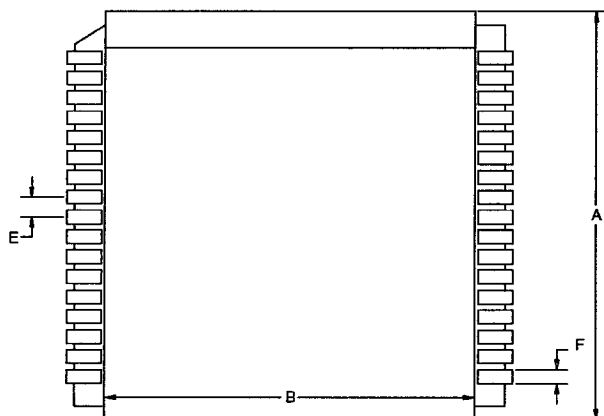


## DS1730Y NONVOLATILE SRAM, 28-PIN 740 MIL EXTENDED MODULE

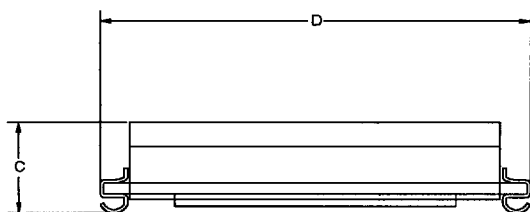


PKG	28-PIN	
DIM	MIN	MAX
A IN. MM	1.480 37.60	1.500 38.10
B IN. MM	0.720 18.29	0.740 18.80
C IN. MM	0.355 9.02	0.375 9.52
D IN. MM	0.080 2.03	0.110 2.79
E IN. MM	0.015 0.38	0.025 0.63
F IN. MM	0.120 3.05	0.160 4.06
G IN. MM	0.090 2.29	0.110 2.79
H IN. MM	0.590 14.99	0.630 16.00
J IN. MM	0.008 0.20	0.012 0.30
K IN. MM	0.015 0.38	0.021 0.53

2614130 0013891 562

**DS1730Y 34-PIN LOW PROFILE MODULE (LPM)**

PKG	INCHES	
DIM	MIN	MAX
A	0.955	0.980
B	0.840	0.855
C	0.290	0.250
D	0.975	0.995
E	0.047	0.053
F	0.015	0.025



Suggested 68-pin PLCC surface mountable sockets with leads on two sides only are:

McKenzie	PLCC34P-SMT-3
Harwin	HIS-40001-04
Robinson Nugent	PLCC-34-SMT
Dallas Semiconductor	DS34PIN-PLC

For recommended prototype/breadboard sockets, contact the Dallas Semiconductor factory.